

NOT RECOMMENDED FOR NEW DESIGN CONTACT US



50V N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(ON)} Max	I _D Max T _A = +25°C
50V	$15m\Omega @ V_{GS} = 10V$	9.1A
307	$23m\Omega @ V_{GS} = 4.5V$	7.4A

Features

- 0.6mm Profile Ideal for Low Profile Applications
- PCB Footprint of 4mm²
- Low Gate Threshold Voltage
- Fast Switching Speed
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. https://www.diodes.com/quality/product-definitions/

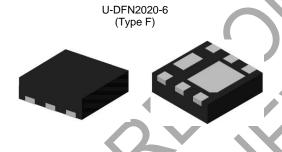
Description and Applications

This MOSFET is designed to minimize the on-state resistance ($R_{\rm DS(ON)}$) yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

- Load Switch
- Adaptor Switch
- Notebook PC

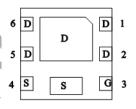
Mechanical Data

- Case: U-DFN2020-6 (Type F)
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 64
- Weight: 0.007 grams (Approximate)

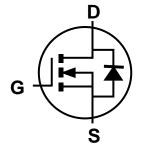


Top View

Bottom View



Pin Out Bottom View



Internal Schematic

Ordering Information (Note 4)

Part Number	Marking	Reel Size (inches)	Quantity per Reel
DMT5015LFDF-7	T5	7	3000
DMT5015LFDF-13	T5	13	10,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.



Marking Information

Site 1:



T5 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: H = 2020) M = Month (ex: 9 = September)

Date Code Key

Year	2013	 2019	2020	2021	2022	2023	2024	2025	2026	2027	2028
Code	Α	 G	Н	- 1	J	K	L	M	N	0	Р

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

Site 2:



T5 = Product Type Marking Code
YWX = Date Code Marking
Y = Year (ex: H = 2020)
W = Week (ex: a = week 27; z represents week 52 and 53)
X = Internal code (ex: U = Monday)

Date Code Key

Year	2020	2021	2022	2023	2024	2025	2026	2027	2028
Code	0	1	2	3	4	5	6	7	8

٧	Neek	1-26		27-52	53
(Code	A-Z	7	a-z	Z

Internal Code	Sun	Mon	Tue	Wed	Thu	Fri	Sat
Code	T	U	V	W	Х	Υ	Z



Maximum Ratings (@ $T_A = +25$ °C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage		V _{DSS}	50	V	
Gate-Source Voltage	V _{GSS}	±16	V		
Continuous Drain Current (Note 6) // 40)/	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I _D	9.1 7.3	Α
Continuous Drain Current (Note 6) V _{GS} = 10V	t<10s	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I _D	11.5 9.2	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%	s)		I _{DM}	60	А
Continuous Source-Drain Diode Current	Is	2.2	Α		
Avalanche Current (Note 7) L = 0.1mH	I _{AS}	14.4	А		
Avalanche Energy (Note 7) L = 0.1mH			E _{AS}	10.4	mJ

Thermal Characteristics

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	PD	0.82	w
Thermal Resistance, Junction to Ambient (Note 5)	Steady State t<10s	R _{θJA}	153 96	°C/W
Total Power Dissipation (Note 6)	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	P _D	1.97 1.2	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State t<10s	R _θ JA	67 42	°C/W
Thermal Resistance, Junction to Case (Note 6)	Steady State	Rejc	14	
Operating and Storage Temperature Range		$T_{J_i} T_{STG}$	-55 to +150	°C

Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition		
OFF CHARACTERISTICS (Note 8)			71					
Drain-Source Breakdown Voltage	BV _{DSS} 4	50	77 –	_	V	$V_{GS} = 0V, I_D = 250\mu A$		
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	-	_	1	μΑ	$V_{DS} = 40V, V_{GS} = 0V$		
Gate-Source Leakage	Igss	/ -	_	±100	nA	$V_{GS} = \pm 16V, V_{DS} = 0V$		
ON CHARACTERISTICS (Note 8)								
Gate Threshold Voltage	$V_{GS(TH)}$	0.5	_	2.0	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$		
Static Drain-Source On-Resistance			10.5	15	mΩ	$V_{GS} = 10V, I_D = 8A$		
Static Drain-Source Off-Resistance	R _{DS} (ON)	_	14	23	11177	$V_{GS} = 4.5V, I_D = 6A$		
Diode Forward Voltage	V_{SD}	_	0.7	1.0	V	$V_{GS} = 0V$, $I_{S} = 5A$		
DYNAMIC CHARACTERISTICS (Note 9)	•							
Input Capacitance	C _{ISS}	_	902.7	_		V _{DS} = 25V, V _{GS} = 0V, f = 1.0MHz		
Output Capacitance	Coss	_	301.4	_	pF			
Reverse Transfer Capacitance	C _{RSS}		15.2			1 = 1.01/11/2		
Gate Resistance	R _G		1.9	1	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$		
Total Gate Charge (V _{GS} = 4.5V)	Q_G	_	6.1	_				
Total Gate Charge (V _{GS} = 10V)	Q_{G}	_	14	_	nC	\/ O5\/ OA		
Gate-Source Charge	Q_{GS}	_	2.4	_	IIC	$V_{DS} = 25V, I_{D} = 8A$		
Gate-Drain Charge	Q_{GD}	_	1.6	_				
Turn-On Delay Time	t _{D(ON)}	_	2.8	_				
Turn-On Rise Time	t _R	_	5.1	_		$V_{DS} = 25V, V_{GS} = 10V,$		
Turn-Off Delay Time	t _{D(OFF)}	_	10.6	_	ns	$R_G = 3\Omega$, $I_D = 8A$		
Turn-Off Fall Time	t _F	_	2.7					
Reverse Recovery Time	t _{RR}	_	18.9	_	ns	I _F = 8A, di/dt = 100A/μs		
Reverse Recovery Charge	Q _{RR}		9.2	_	nC	I _F = 8A, di/dt = 100A/μs		

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

^{6.} Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

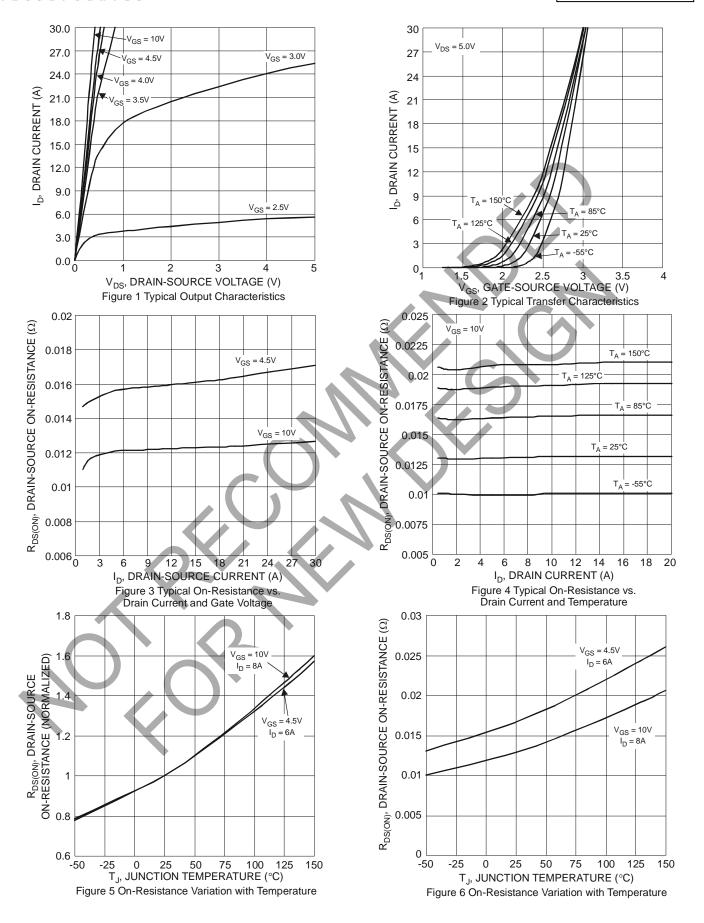
^{7.} I_{AS} and E_{AS} rating are based on low frequency and duty cycles to keep T_J = +25°C.

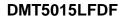
^{8.} Short duration pulse test used to minimize self-heating effect.

^{9.} Guaranteed by design. Not subject to product testing.











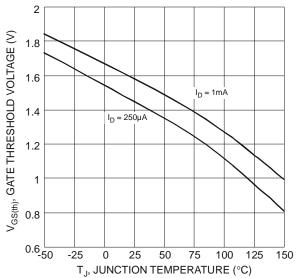
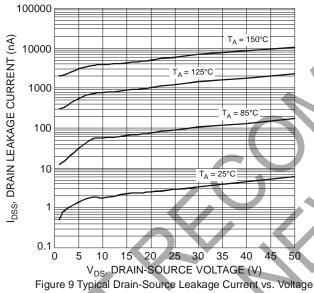
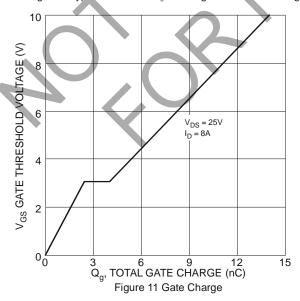
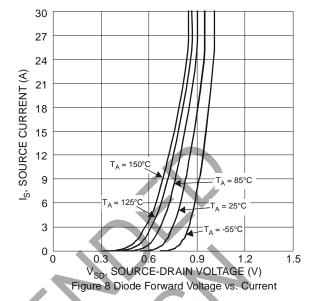
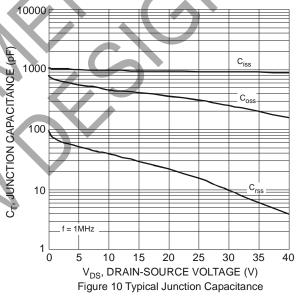


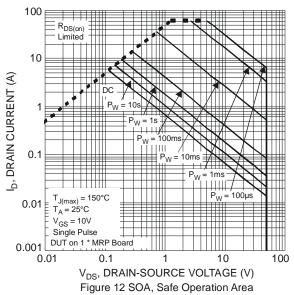
Figure 7 Gate Threshold Variation vs. Ambient Temperature



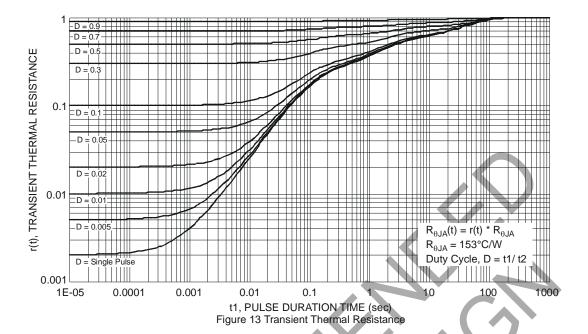










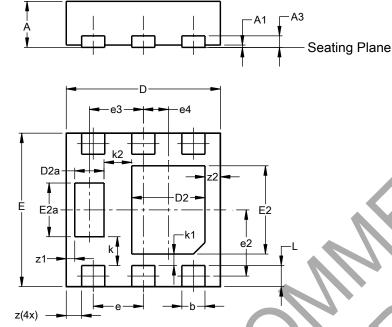




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-6 (Type F)

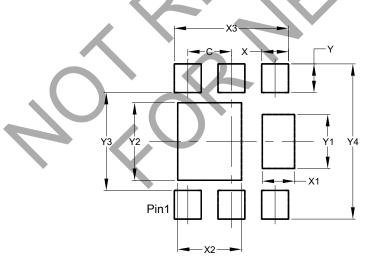


	_	12020-6 be F)					
Dim	Min	Max	Тур				
Α	0.57	0.63	0.60				
A1	0.00	0.05	0.03				
A3	-	-	0.15				
b	0.25	0.35	0.30				
D	1.95	2.05	2.00				
D2	0.85	0.85 1.05 0.95					
D2a	0.33 0.43 0.38						
E	1.95	2.05	2.00				
E2	1.05	1.25	1.15				
E2a	0.65	0.75	0.70				
е		0.65 BS	С				
e2	().863 BS	SC				
е3		0.70 BS	С				
e4).325 BS					
k		0.37 BS					
k1		0.15 BS					
k2		0.36 BS					
L		0.325					
z		0.20 BSC					
z 1).110 BS					
z2		0.20 BS	С				
All C	Dimens	ions in	mm				

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-6 (Type F)



Dimensions	Value (in mm)
С	0.650
Х	0.400
X1	0.480
X2	0.950
Х3	1.700
Y	0.425
Y1	0.800
Y2	1.150
Y3	1.450
Y4	2.300



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